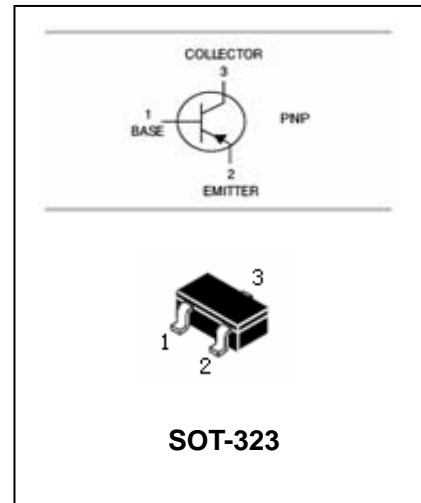


## PNP Silicon Epitaxial Planar Transistor

## 2SA1579W

### FEATURES

- Power dissipation.( $P_C=200\text{mW}$ )
- Excellent  $H_{FE}$  Linearity.



### APPLICATIONS

- General purpose application.

### ORDERING INFORMATION

| Type No. | Marking  | Package Code |
|----------|----------|--------------|
| 2SA1579W | HP/HQ/HR | SOT-323      |

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

| Symbol         | Parameter                        | Value   | Units            |
|----------------|----------------------------------|---------|------------------|
| $V_{CBO}$      | Collector-Base Voltage           | -120    | V                |
| $V_{CEO}$      | Collector-Emitter Voltage        | -120    | V                |
| $V_{EBO}$      | Emitter-Base Voltage             | -5      | V                |
| $I_C$          | Collector Current -Continuous    | -50     | mA               |
| $P_C$          | Collector Dissipation            | 200     | mW               |
| $T_j, T_{stg}$ | Junction and Storage Temperature | -55~150 | $^\circ\text{C}$ |

**PNP Silicon Epitaxial Planar Transistor****2SA1579W****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

| Parameter                            | Symbol        | Test conditions                      | MIN  | TYP | MAX  | UNIT    |
|--------------------------------------|---------------|--------------------------------------|------|-----|------|---------|
| Collector-base breakdown voltage     | $V_{(BR)CBO}$ | $I_C=-50\mu A, I_E=0$                | -120 |     |      | V       |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$ | $I_C=-1mA, I_B=0$                    | -120 |     |      | V       |
| Emitter-base breakdown voltage       | $V_{(BR)EBO}$ | $I_E=-50\mu A, I_C=0$                | -5   |     |      | V       |
| Collector cut-off current            | $I_{CBO}$     | $V_{CB}=-100V, I_E=0$                |      |     | -0.5 | $\mu A$ |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB}=-4V, I_C=0$                  |      |     | -0.5 | $\mu A$ |
| DC current gain                      | $h_{FE}$      | $V_{CE}=-6V, I_C=-2mA$               | 180  |     | 560  |         |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C=-10mA, I_B=-1mA$                |      |     | -0.5 | V       |
| Transition frequency                 | $f_T$         | $V_{CE}=-12V, I_C=-2mA$<br>$f=30MHz$ |      | 140 |      | MHz     |
| Collector output capacitance         | $C_{ob}$      | $V_{CB}=-12V, I_E=0, f=1MHz$         |      | 3.2 |      | pF      |

**CLASSIFICATION OF  $h_{FE}$** 

| Rank    | S       | R       |
|---------|---------|---------|
| Range   | 180-390 | 270-560 |
| marking | RR      | RS      |

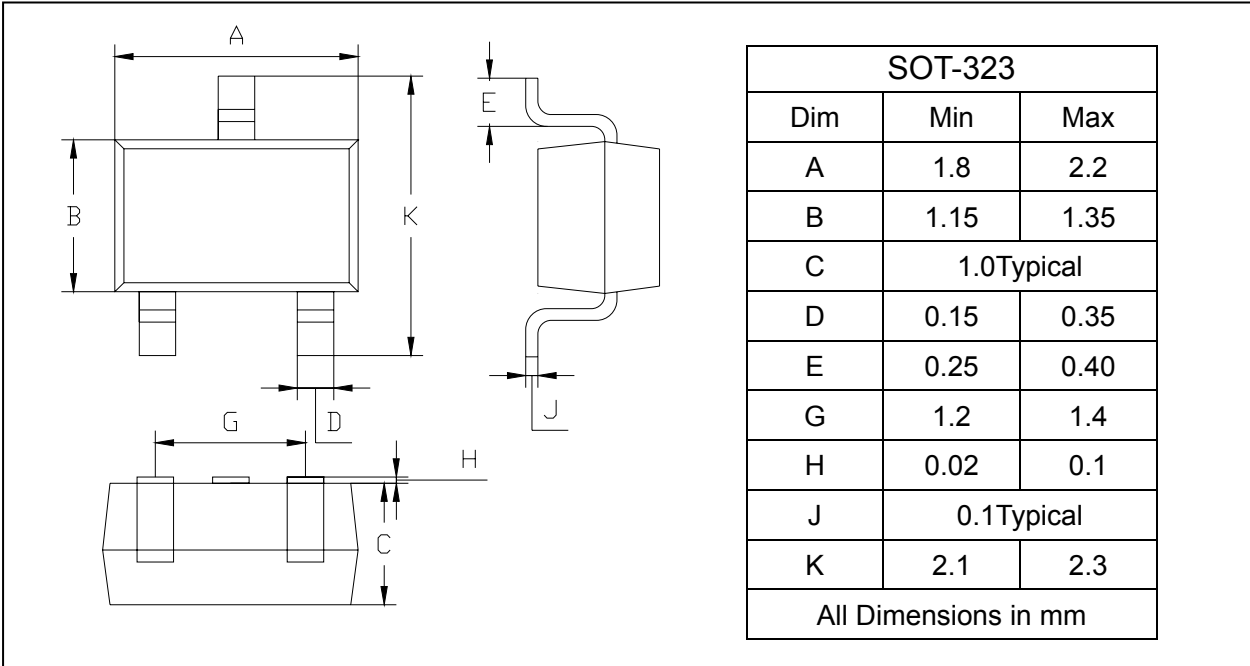
## PNP Silicon Epitaxial Planar Transistor

## 2SA1579W

### PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



### PACKAGE INFORMATION

| Device   | Package | Shipping       |
|----------|---------|----------------|
| 2SA1579W | SOT-323 | 3000/Tape&Reel |